

www.vishay.com

Vishay Semiconductors

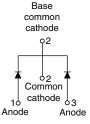
Hyperfast Rectifier, 2 x 15 FRED Pt®





TO-220AB

TO-220 FULL-PAK





VS-30CTH02PbF VS-30CTH02-N3

VS-30CTH02FPPbF VS-30CTH02FP-N3

PRODUCT SUMMARY						
Package TO-220AB, TO-220Fl						
I _{F(AV)}	2 x 15 A					
V_{R}	200 V					
V _F at I _F	1.05 V					
t _{rr} typ.	See Recovery table					
T _J max.	175 °C					
Diode variation	Common cathode					

FEATURES

- · Hyperfast recovery time
- · Low forward voltage drop
- 175 °C operating junction temperature
- · Low leakage current
- Fully isolated package (V_{INS} = 2500 V_{RMS})
- UL E78996 pending
- Compliant to RoHS Directive 2002/95/EC
- Designed and qualified according to JEDEC-JESD47
- Halogen-free according to IEC 61249-2-21 definition (-N3 only)





HALOGEN FREE

DESCRIPTION/APPLICATIONS

200 V series are the state of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS								
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Peak repetitive reverse voltage		V _{RRM}		200	V			
Average rectified forward current	per diode	I _{F(AV)}	T _C = 159 °C	- 15 30	A			
	(FULL-PAK) per diode		T _C = 125 °C					
	per device							
Non-repetitive peak surge current		I _{FSM}	T _J = 25 °C	200				
Operating junction and storage temperatures		T _J , T _{Stg}		- 65 to 175	°C			

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	200	-	-			
Forward voltage	V _F	I _F = 15 A	-	0.92	1.05	V		
		I _F = 15 A, T _J = 125 °C	-	0.78	0.85			
Poverse leekage current		$V_R = V_R$ rated	-	-	10			
Reverse leakage current	I _R	$T_J = 125 ^{\circ}\text{C}, V_R = V_R \text{rated}$	-	5	300	μA		
Junction capacitance	C _T	V _R = 200 V	-	57	-	pF		
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8	-	nH		



www.vishay.com

Vishay Semiconductors

DYNAMIC RECOVERY CHARACTERISTICS (T _C = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS		
Reverse recovery time		$I_F = 1 A, dI_F/dt = 50$	A/μs, V _R = 30 V	-	-	35		
		$I_F = 1 \text{ A, } dI_F/dt = 100 \text{ A/}\mu\text{s, } V_R = 30 \text{ V}$		-	-	30	200	
	t _{rr}	T _J = 25 °C	$I_F = 15 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_B = 160 \text{ V}$	-	26	-	ns	
		T _J = 125 °C		-	40	-		
Peak recovery current	I _{RRM}	T _J = 25 °C		-	2.8	-	^	
		T _J = 125 °C		-	6.0	-	Α	
Reverse recovery charge	0	T _J = 25 °C		-	37	-	nC	
	Q _{rr}	T _J = 125 °C		-	120	-	110	

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	PARAMETER		TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Maximum junction ar temperature range	nd storage	T _J , T _{Stg}		- 65	-	175	°C		
Thermal resistance,	per diode	R _{th.IC}	Mounting surface, flat, smooth and greased	-	-	1.1	°C/W		
junction to case (FULL-PAK)	(FULL-PAK) per diode			-	-	3.5	O/ VV		
Marking device			Case style TO-220AB	30CTH02					
			Case style TO-220 FULL-PAK	30CTH02FP					

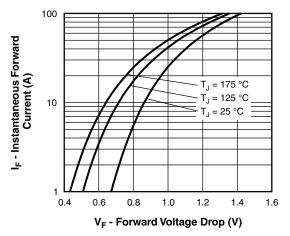


Fig. 1 - Typical Forward Voltage Drop Characteristics

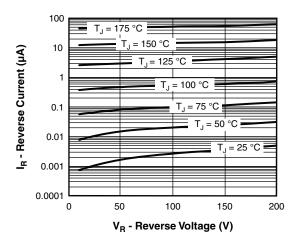


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

www.vishay.com

Vishay Semiconductors

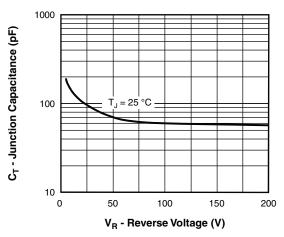


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

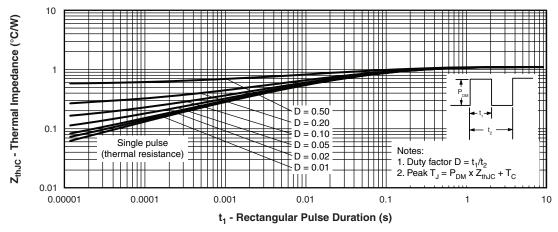


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

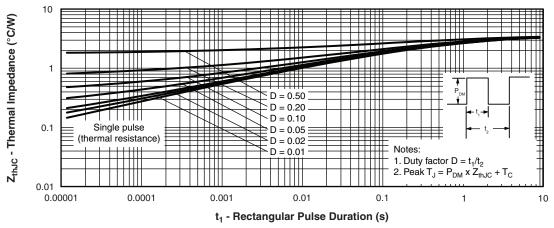


Fig. 5 - Maximum Thermal Impedance Z_{thJC} Characteristics (FULL-PAK)

www.vishay.com

Vishay Semiconductors

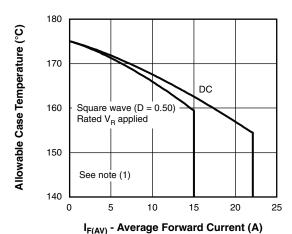


Fig. 6 - Maximum Allowable Case Temperature vs. Average Forward Current

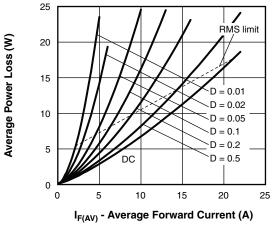


Fig. 8 - Forward Power Loss Characteristics

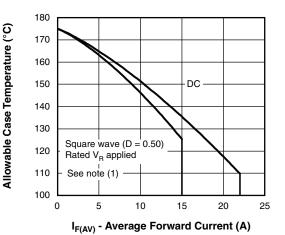


Fig. 7 - Maximum Allowable Case Temperature vs. Average Forward Current (FULL-PAK)

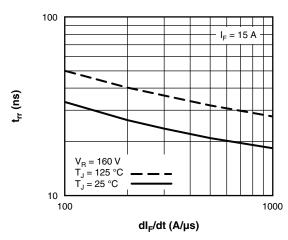


Fig. 9 - Typical Reverse Recovery Time vs. dl_F/dt

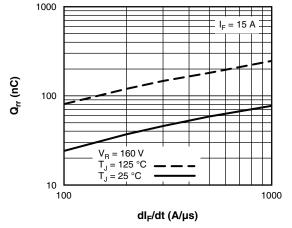


Fig. 10 - Typical Stored Charge vs. dI_F/dt

Note

(1) Formula used: T_C = T_J - (Pd + Pd_{REV}) x R_{thJC}; Pd = Forward power loss = I_{F(AV)} x V_{FM} at (I_{F(AV)}/D) (see fig. 8); Pd_{REV} = Inverse power loss = V_{R1} x I_R (1 - D); I_R at V_{R1} = Rated V_R

www.vishay.com

Vishay Semiconductors

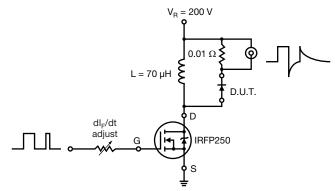
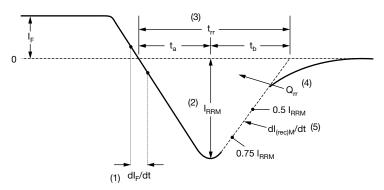


Fig. 11 - Reverse Recovery Parameter Test Circuit



- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

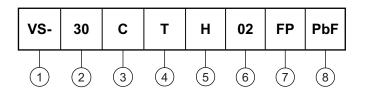
(5) $dl_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 12 - Reverse Recovery Waveform and Definitions

Vishay Semiconductors

ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

Current rating (30 = 30 A)

3 - C = Common cathode

4 - T = TO-220

5 - H = Hyperfast recovery

Voltage rating (02 = 200 V)

7 - • None = TO-220AB

• FP = TO-220 FULL-PAK

8 - Environmental digit:

PbF = Lead (Pb)-free and RoHS compliant

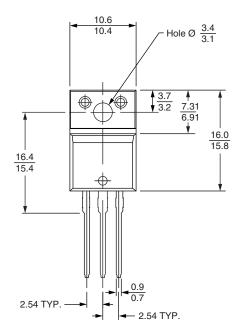
-N3 = Halogen-free, RoHS compliant and totally lead (Pb)-free

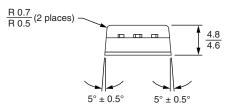
ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-20CTH03PbF	50	1000	Antistatic plastic tube				
VS-20CTH03-N3	50	1000	Antistatic plastic tube				
VS-20CTH03FPPbF	50	1000	Antistatic plastic tube				
VS-20CTH03FP-N3	50	1000	Antistatic plastic tube				

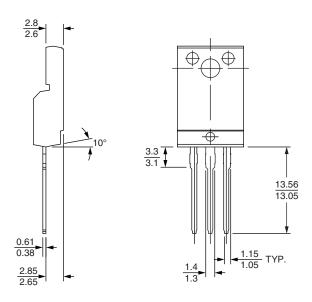
LINKS TO RELATED DOCUMENTS						
Dimensions	TO-220AB	www.vishay.com/doc?95222				
Dimensions	TO-220FP	www.vishay.com/doc?95072				
	TO-220ABPbF	www.vishay.com/doc?95225				
Part marking information	TO-220AB-N3	www.vishay.com/doc?95028				
Part marking information	TO-220FPPbF	www.vishay.com/doc?95069				
	TO-220FP-N3	www.vishay.com/doc?95456				

Vishay Semiconductors

DIMENSIONS in millimeters







Lead assignments

Diodes

- 1. Anode/open
- 2. Cathode
- 3. Anode

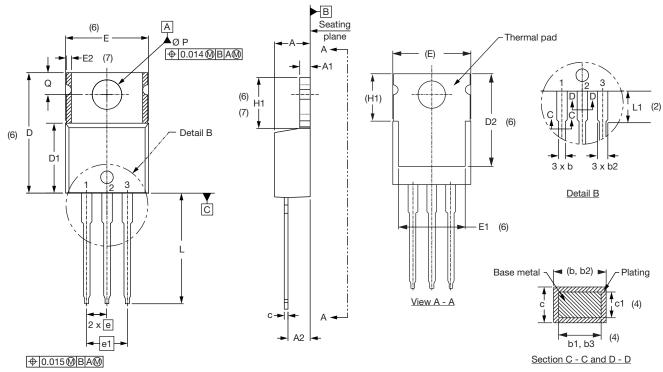
Conforms to JEDEC outline TO-220 FULL-PAK



Vishay Semiconductors

TO-220AB

DIMENSIONS in millimeters and inches



Lead tip

Lead assignments

<u>Diodes</u>

- 1. Anode/open
- 2. Cathode
- 3. Anode

Conforms to JEDEC outline TO-220AB

SYMBOL	MILLIN	MILLIMETERS		INCHES	
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6

SYMBOL	MILLIM	IETERS	INC	HES	NOTES
STIMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
E	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
E2	-	0.76	-	0.030	7
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6, 7
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
ØΡ	3.54	3.73	0.139	0.147	
Q	2.60	3.00	0.102	0.118	
θ	90° to 93°		90° t	o 93°	

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline



Legal Disclaimer Notice

Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk and agree to fully indemnify and hold Vishay and its distributors harmless from and against any and all claims, liabilities, expenses and damages arising or resulting in connection with such use or sale, including attorneys fees, even if such claim alleges that Vishay or its distributor was negligent regarding the design or manufacture of the part. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Material Category Policy

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.